

Atty Docket No.: TKHR4580

Serial No.: 09/479,483

**In The Claims:**

1. (currently amended) A fabrication method for a multi-layered thin film protective layer, which is applicable to a substrate comprising a first device area and a second device area, the method comprising the steps of:

forming a first protective layer on the first device area, wherein the first protective layer prevents the first device area from moisture and scratch;

forming a plurality of material structures on the first protective layer, the material structures and the underlying first protective layer together formed as first pad spacers;

forming a plurality of upper oxide material/silicon nitride/bottom oxide material structures on the second device area as second pad spacers in the second device area, wherein the second pad spacers are higher than the first protective layer; and

forming a second protective layer for at least covering the second device area, wherein a transmittance of the second protective layer is higher than transmittance of the first protective layer under a visible light range.

2. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim 1, further including:

forming sequentially a first oxide layer, a silicon nitride layer and a second oxide layer on the substrate;

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patterning the second oxide ~~layer material~~ to form the material structures and an upper oxide material of the material of the upper oxide material/silicon nitride/bottom oxide material structures;

patterning the silicon nitride layer and the first oxide layer to form a silicon nitride/oxide material structure as the first protective layer in the first device area and to form a bottom oxide material and a silicon nitride layer of the upper oxide material/silicon nitride/bottom oxide material structures; and

forming a third oxide layer on the substrate as a the second protective layer.

3. (previously amended) The fabrication method for a multi-layered thin film protective layer according to claim 2, wherein the transmittance of the second protective layer is approximately 85%.

4. (previously amended) The fabrication method for a multi-layered thin film protective layer according to claim 2, wherein the third oxide layer is approximately 500Å thick.

5. (previously amended) The fabrication method for a multi-layered thin film protective layer according to claim 2, wherein the third oxide layer includes tetra-ethyl-ortho-silicate.

**Claims 6-17 (canceled)**

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18. (currently amended) A fabrication method for a multi-layered thin film protective layer, which is applicable to a substrate comprising a first device area and a second device area, the method comprising the steps of:

forming a first protective layer on the first device area, wherein the first protective layer prevents the first device area from moisture and scratch;

forming a plurality of material structures on the first protective layer, the material structures and the underlying first protective layer together formed as first pad spacers;

forming a plurality of multi-layered material structures on the second device area as second pad spacers in the second device area, wherein the second pad spacers are higher than the first protective layer; and

forming a second protective layer at least covering the second device area, wherein a transmittance of the second protective layer is higher than a transmittance of the first protective layer under a visible light range.

19. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim 18, further including:

forming sequentially a first material layer, a second material layer and a third material layer on the substrate;

patterning the third material layer to form the material structures and an upper layer of the multi-layered material structures;

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patterning the second layer and the first layer to form the first protective layer in the first device area and to form ~~the~~ a bottom layers and a center layer of the ~~material/silicon nitride/oxide~~ multi-layered material structures in the second device area; and

forming a ~~second protective-fourth material~~ layer covering at least the first device area ~~and the second device area, wherein as the second protective layer-second protective layer.~~

20. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim 18, wherein the second protective layer is thinner than the upper layer, the center layer or the bottom ~~any layers~~ of the multi-layered material structures.

21. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim 18, wherein the first protective layer at least comprises an oxide layer and a silicon oxide nitride layer ~~on the oxide layer.~~

22. (previously amended) The fabrication method for a multi-layered thin film protective layer according to claim 18, wherein the second protective layer comprises an oxide layer.